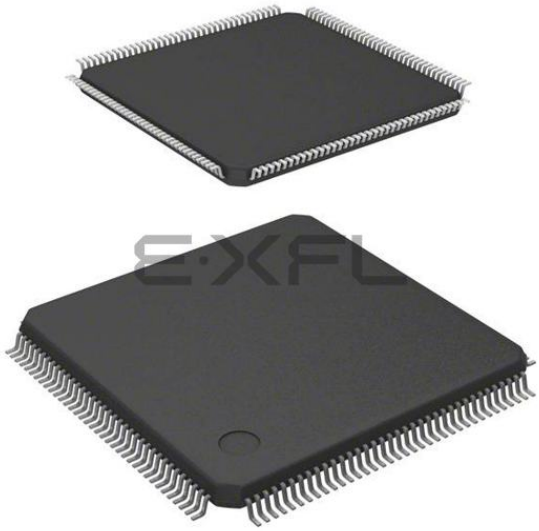

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Applications of "Embedded - Microcontrollers"

Details	
Product Status	Active
Core Processor	ARM® Cortex®-M4
Core Size	32-Bit Single-Core
Speed	168MHz
Connectivity	CANbus, EBI/EMI, I²C, IrDA, LINbus, SPI, UART/USART, USB OTG
Peripherals	Brown-out Detect/Reset, DMA, I²S, LCD, POR, PWM, WDT
Number of I/O	114
Program Memory Size	1MB (1M x 8)
Program Memory Type	FLASH
EEPROM Size	-
RAM Size	192K x 8
Voltage - Supply (Vcc/Vdd)	1.8V ~ 3.6V
Data Converters	A/D 24x12b; D/A 2x12b
Oscillator Type	Internal
Operating Temperature	-40°C ~ 85°C (TA)
Mounting Type	Surface Mount
Package / Case	144-LQFP
Supplier Device Package	144-LQFP (20x20)
Purchase URL	https://www.e-xfl.com/product-detail/stmicroelectronics/stm32f405zgt6v

Two external ceramic capacitors should be connected on V_{CAP_1} & V_{CAP_2} pin. Refer to *Figure 21: Power supply scheme* and *Figure 16: VCAP_1/VCAP_2 operating conditions*.

All packages have regulator ON feature.

Regulator OFF

This feature is available only on packages featuring the BYPASS_REG pin. The regulator is disabled by holding BYPASS_REG high. The regulator OFF mode allows to supply externally a V_{12} voltage source through V_{CAP_1} and V_{CAP_2} pins.

Since the internal voltage scaling is not manage internally, the external voltage value must be aligned with the targeted maximum frequency. Refer to *Table 14: General operating conditions*.

The two 2.2 µF ceramic capacitors should be replaced by two 100 nF decoupling capacitors.

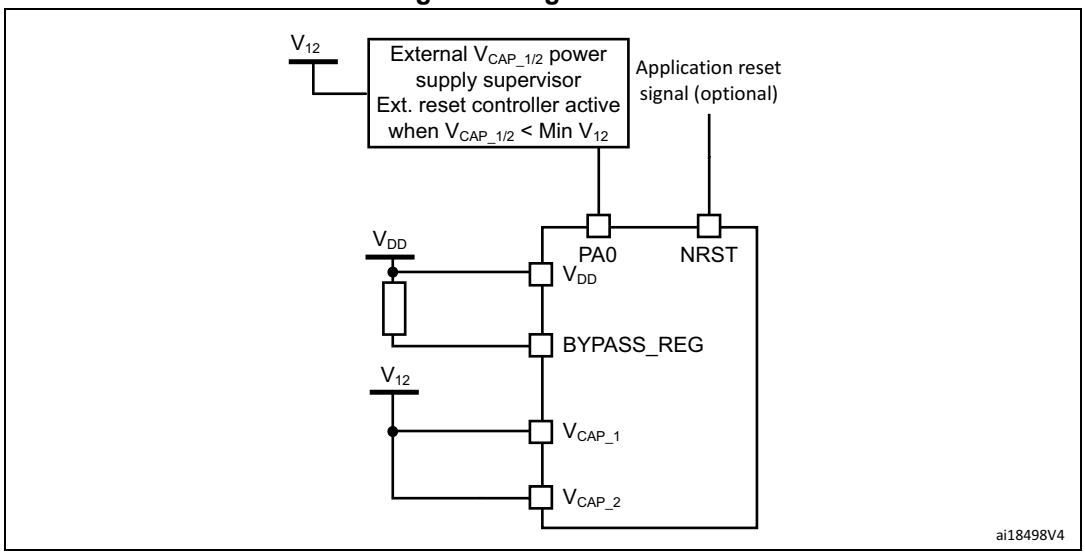
Refer to *Figure 21: Power supply scheme*

When the regulator is OFF, there is no more internal monitoring on V_{12}. An external power supply supervisor should be used to monitor the V_{12} of the logic power domain. PA0 pin should be used for this purpose, and act as power-on reset on V_{12} power domain.

In regulator OFF mode the following features are no more supported:

- PA0 cannot be used as a GPIO pin since it allows to reset a part of the V_{12} logic power domain which is not reset by the NRST pin.
- As long as PA0 is kept low, the debug mode cannot be used under power-on reset. As a consequence, PA0 and NRST pins must be managed separately if the debug connection under reset or pre-reset is required.
- The standby mode is not available

Figure 9. Regulator OFF



has a typical frequency of 32 kHz. The RTC can be calibrated using an external 512 Hz output to compensate for any natural quartz deviation.

Two alarm registers are used to generate an alarm at a specific time and calendar fields can be independently masked for alarm comparison. To generate a periodic interrupt, a 16-bit programmable binary auto-reload downcounter with programmable resolution is available and allows automatic wakeup and periodic alarms from every 120 µs to every 36 hours.

A 20-bit prescaler is used for the time base clock. It is by default configured to generate a time base of 1 second from a clock at 32.768 kHz.

The 4-Kbyte backup SRAM is an EEPROM-like memory area. It can be used to store data which need to be retained in V_{BAT} and standby mode. This memory area is disabled by default to minimize power consumption (see *Section 2.2.19: Low-power modes*). It can be enabled by software.

The backup registers are 32-bit registers used to store 80 bytes of user application data when V_{DD} power is not present. Backup registers are not reset by a system, a power reset, or when the device wakes up from the Standby mode (see *Section 2.2.19: Low-power modes*).

Additional 32-bit registers contain the programmable alarm subseconds, seconds, minutes, hours, day, and date.

Like backup SRAM, the RTC and backup registers are supplied through a switch that is powered either from the V_{DD} supply when present or from the V_{BAT} pin.

2.2.19 Low-power modes

The STM32F405xx and STM32F407xx support three low-power modes to achieve the best compromise between low-power consumption, short startup time and available wakeup sources:

- **Sleep mode**

  In Sleep mode, only the CPU is stopped. All peripherals continue to operate and can wake up the CPU when an interrupt/event occurs.

- **Stop mode**

  The Stop mode achieves the lowest power consumption while retaining the contents of SRAM and registers. All clocks in the V_{12} domain are stopped, the PLL, the HSI RC and the HSE crystal oscillators are disabled. The voltage regulator can also be put either in normal or in low-power mode.

  The device can be woken up from the Stop mode by any of the EXTI line (the EXTI line source can be one of the 16 external lines, the PVD output, the RTC alarm / wakeup / tamper / time stamp events, the USB OTG FS/HS wakeup or the Ethernet wakeup).

- **Standby mode**

  The Standby mode is used to achieve the lowest power consumption. The internal voltage regulator is switched off so that the entire V_{12} domain is powered off. The PLL, the HSI RC and the HSE crystal oscillators are also switched off. After entering

Standby mode, the SRAM and register contents are lost except for registers in the backup domain and the backup SRAM when selected.

The device exits the Standby mode when an external reset (NRST pin), an IWDG reset, a rising edge on the WKUP pin, or an RTC alarm / wakeup / tamper /time stamp event occurs.

The standby mode is not supported when the embedded voltage regulator is bypassed and the V_{12} domain is controlled by an external power.

2.2.20 V_{BAT} operation

The V_{BAT} pin allows to power the device V_{BAT} domain from an external battery, an external supercapacitor, or from V_{DD} when no external battery and an external supercapacitor are present.

V_{BAT} operation is activated when V_{DD} is not present.

The V_{BAT} pin supplies the RTC, the backup registers and the backup SRAM.

Note: When the microcontroller is supplied from V_{BAT}, external interrupts and RTC alarm/events do not exit it from V_{BAT} operation.

When PDR_ON pin is not connected to V_{DD} (internal reset OFF), the V_{BAT} functionality is no more available and V_{BAT} pin should be connected to V_{DD}.

2.2.21 Timers and watchdogs

The STM32F405xx and STM32F407xx devices include two advanced-control timers, eight general-purpose timers, two basic timers and two watchdog timers.

All timer counters can be frozen in debug mode.

Table 4 compares the features of the advanced-control, general-purpose and basic timers.

Table 4. Timer feature comparison

Timer type	Timer	Counter resolution	Counter type	Prescaler factor	DMA request generation	Capture/ compare channels	Complemen-tary output	Max interface clock (MHz)	Max timer clock (MHz)
Advanced -control	TIM1, TIM8	16-bit	Up, Down, Up/down	Any integer between 1 and 65536	Yes	4	Yes	84	168

Table 7. STM32F40xxx pin and ball definitions (continued)

Pin number						Pin name (function after reset)[1]	Pin type	I / O structure	Notes	Alternate functions	Additional functions
LQFP64	WLCSP90	LQFP100	LQFP144	UFBGA176	LQFP176						
-	-	-	49	R6	59	PF11	I/O	FT	-	DCMI_D12/ EVENTOUT	-
-	-	-	50	P6	60	PF12	I/O	FT	-	FSMC_A6/ EVENTOUT	-
-	-	-	51	M8	61	V_{SS}	S	-	-	-	-
-	-	-	52	N8	62	V_{DD}	S	-	-	-	-
-	-	-	53	N6	63	PF13	I/O	FT	-	FSMC_A7/ EVENTOUT	-
-	-	-	54	R7	64	PF14	I/O	FT	-	FSMC_A8/ EVENTOUT	-
-	-	-	55	P7	65	PF15	I/O	FT	-	FSMC_A9/ EVENTOUT	-
-	-	-	56	N7	66	PG0	I/O	FT	-	FSMC_A10/ EVENTOUT	-
-	-	-	57	M7	67	PG1	I/O	FT	-	FSMC_A11/ EVENTOUT	-
-	G6	38	58	R8	68	PE7	I/O	FT	-	FSMC_D4/TIM1_ETR/ EVENTOUT	-
-	H6	39	59	P8	69	PE8	I/O	FT	-	FSMC_D5/ TIM1_CH1N/ EVENTOUT	-
-	J6	40	60	P9	70	PE9	I/O	FT	-	FSMC_D6/TIM1_CH1/ EVENTOUT	-
-	-	-	61	M9	71	V_{SS}	S	-	-	-	-
-	-	-	62	N9	72	V_{DD}	S	-	-	-	-
-	F6	41	63	R9	73	PE10	I/O	FT	-	FSMC_D7/TIM1_CH2N/ EVENTOUT	-
-	J5	42	64	P10	74	PE11	I/O	FT	-	FSMC_D8/TIM1_CH2/ EVENTOUT	-
-	H5	43	65	R10	75	PE12	I/O	FT	-	FSMC_D9/TIM1_CH3N/ EVENTOUT	-
-	G5	44	66	N11	76	PE13	I/O	FT	-	FSMC_D10/TIM1_CH3/ EVENTOUT	-
-	F5	45	67	P11	77	PE14	I/O	FT	-	FSMC_D11/TIM1_CH4/ EVENTOUT	-
-	G4	46	68	R11	78	PE15	I/O	FT	-	FSMC_D12/TIM1_BKIN/ EVENTOUT	-

Table 7. STM32F40xxx pin and ball definitions (continued)

Pin number						Pin name (function after reset)(1)	Pin type	I / O structure	Notes	Alternate functions	Additional functions
LQFP64	WLCSP90	LQFP100	LQFP144	UFBGA176	LQFP176						
55	B6	89	133	A10	161	PB3 (JTDO/ TRACESWO)	I/O	FT	-	JTDO/ TRACESWO/ SPI3_SCK / I2S3_CK / TIM2_CH2 / SPI1_SCK/ EVENTOUT	-
56	A6	90	134	A9	162	PB4 (NJTRST)	I/O	FT	-	NJTRST/ SPI3_MISO / TIM3_CH1 / SPI1_MISO / I2S3ext_SD/ EVENTOUT	-
57	D7	91	135	A6	163	PB5	I/O	FT	-	I2C1_SMBA/ CAN2_RX / OTG_HS_ULPI_D7 / ETH_PPS_OUT/TIM3_CH2 / SPI1_MOSI/ SPI3_MOSI / DCMI_D10 / I2S3_SD/ EVENTOUT	-
58	C7	92	136	B6	164	PB6	I/O	FT	-	I2C1_SCL/ TIM4_CH1 / CAN2_TX / DCMI_D5/USART1_TX/ EVENTOUT	-
59	B7	93	137	B5	165	PB7	I/O	FT	-	I2C1_SDA / FSMC_NL / DCMI_VSYNC / USART1_RX/ TIM4_CH2/ EVENTOUT	-
60	A7	94	138	D6	166	BOOT0	I	B	-	-	V_{PP}
61	D8	95	139	A5	167	PB8	I/O	FT	-	TIM4_CH3/SDIO_D4/ TIM10_CH1 / DCMI_D6 / ETH_MII_TXD3 / I2C1_SCL/ CAN1_RX/ EVENTOUT	-
62	C8	96	140	B4	168	PB9	I/O	FT	-	SPI2_NSS/ I2S2_WS / TIM4_CH4/ TIM11_CH1/ SDIO_D5 / DCMI_D7 / I2C1_SDA / CAN1_TX/ EVENTOUT	-
-	-	97	141	A4	169	PE0	I/O	FT	-	TIM4_ETR / FSMC_NBL0 / DCMI_D2/ EVENTOUT	-
-	-	98	142	A3	170	PE1	I/O	FT	-	FSMC_NBL1 / DCMI_D3/ EVENTOUT	-
63	-	99	-	D5	-	V_{SS}	S	-	-	-	-

5 Electrical characteristics

5.1 Parameter conditions

Unless otherwise specified, all voltages are referenced to V_{SS}.

5.1.1 Minimum and maximum values

Unless otherwise specified the minimum and maximum values are guaranteed in the worst conditions of ambient temperature, supply voltage and frequencies by tests in production on 100% of the devices with an ambient temperature at T_A = 25 °C and T_A = $T_A$max (given by the selected temperature range).

Data based on characterization results, design simulation and/or technology characteristics are indicated in the table footnotes and are not tested in production. Based on characterization, the minimum and maximum values refer to sample tests and represent the mean value plus or minus three times the standard deviation (mean±3Σ).

5.1.2 Typical values

Unless otherwise specified, typical data are based on T_A = 25 °C, V_{DD} = 3.3 V (for the 1.8 V ≤V_{DD} ≤3.6 V voltage range). They are given only as design guidelines and are not tested.

Typical ADC accuracy values are determined by characterization of a batch of samples from a standard diffusion lot over the full temperature range, where 95% of the devices have an error less than or equal to the value indicated (mean±2Σ).

5.1.3 Typical curves

Unless otherwise specified, all typical curves are given only as design guidelines and are not tested.

5.1.4 Loading capacitor

The loading conditions used for pin parameter measurement are shown in *Figure 19*.

5.1.5 Pin input voltage

The input voltage measurement on a pin of the device is described in *Figure 20*.

Figure 19. Pin loading conditions

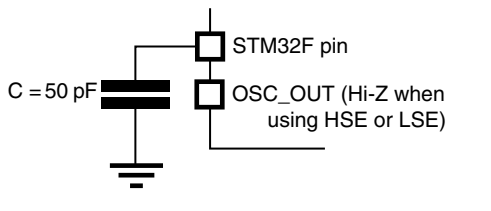
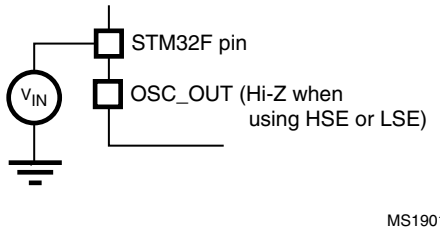


Figure 20. Pin input voltage



5.3.5 Embedded reset and power control block characteristics

The parameters given in *Table 19* are derived from tests performed under ambient temperature and V_{DD} supply voltage conditions summarized in *Table 14*.

Table 19. Embedded reset and power control block characteristics

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
V_{PVD}	Programmable voltage detector level selection	PLS[2:0]=000 (rising edge)	2.09	2.14	2.19	V
		PLS[2:0]=000 (falling edge)	1.98	2.04	2.08	V
		PLS[2:0]=001 (rising edge)	2.23	2.30	2.37	V
		PLS[2:0]=001 (falling edge)	2.13	2.19	2.25	V
		PLS[2:0]=010 (rising edge)	2.39	2.45	2.51	V
		PLS[2:0]=010 (falling edge)	2.29	2.35	2.39	V
		PLS[2:0]=011 (rising edge)	2.54	2.60	2.65	V
		PLS[2:0]=011 (falling edge)	2.44	2.51	2.56	V
		PLS[2:0]=100 (rising edge)	2.70	2.76	2.82	V
		PLS[2:0]=100 (falling edge)	2.59	2.66	2.71	V
		PLS[2:0]=101 (rising edge)	2.86	2.93	2.99	V
		PLS[2:0]=101 (falling edge)	2.65	2.84	2.92	V
		PLS[2:0]=110 (rising edge)	2.96	3.03	3.10	V
		PLS[2:0]=110 (falling edge)	2.85	2.93	2.99	V
		PLS[2:0]=111 (rising edge)	3.07	3.14	3.21	V
		PLS[2:0]=111 (falling edge)	2.95	3.03	3.09	V
$V_{PVDhyst}$(1)	PVD hysteresis	-	-	100	-	mV
$V_{POR/PDR}$	Power-on/power-down reset threshold	Falling edge	1.60	1.68	1.76	V
		Rising edge	1.64	1.72	1.80	V
$V_{PDRhyst}$(1)	PDR hysteresis	-	-	40	-	mV
V_{BOR1}	Brownout level 1 threshold	Falling edge	2.13	2.19	2.24	V
		Rising edge	2.23	2.29	2.33	V

Table 21. Typical and maximum current consumption in Run mode, code with data processing running from Flash memory (ART accelerator disabled)

Symbol	Parameter	Conditions	f_{HCLK}	Typ	Max(1)		Unit
				T_A = 25 °C	T_A = 85 °C	T_A = 105 °C	
I_{DD}	Supply current in Run mode	External clock(2), all peripherals enabled(3)(4)	168 MHz	93	109	117	mA
			144 MHz	76	89	96	
			120 MHz	67	79	86	
			90 MHz	53	65	73	
			60 MHz	37	49	56	
			30 MHz	20	32	39	
			25 MHz	16	27	35	
			16 MHz	11	23	30	
			8 MHz	6	18	25	
			4 MHz	4	16	23	
			2 MHz	3	15	22	
		External clock(2), all peripherals disabled(3)(4)	168 MHz	46	61	69	
			144 MHz	40	52	60	
			120 MHz	37	48	56	
			90 MHz	30	42	50	
			60 MHz	22	33	41	
			30 MHz	12	24	31	
			25 MHz	10	21	29	
			16 MHz	7	19	26	
			8 MHz	4	16	23	
			4 MHz	3	15	22	
			2 MHz	2	14	21	

1. Guaranteed by characterization, tested in production at V_{DD} max and f_{HCLK} max with peripherals enabled.
2. External clock is 4 MHz and PLL is on when f_{HCLK} > 25 MHz.
3. When analog peripheral blocks such as (ADCs, DACs, HSE, LSE, HSI,LSI) are on, an additional power consumption should be considered.
4. When the ADC is ON (ADON bit set in the ADC_CR2 register), add an additional power consumption of 1.6 mA per ADC for the analog part.

With a modulation depth (md) = ±2 % (4 % peak to peak), and PLLN = 240 (in MHz):

$$\text{INCSTEP} = \text{round}[((2^{15}-1)\times 2\times 240)/\ (100\times 5\times 250)] = 126\text{md(quantitazed)}\%$$

An amplitude quantization error may be generated because the linear modulation profile is obtained by taking the quantized values (rounded to the nearest integer) of MODPER and INCSTEP. As a result, the achieved modulation depth is quantized. The percentage quantized modulation depth is given by the following formula:

$$\text{md}_{\text{quantized}}\% = (\text{MODEPER}\times \text{INCSTEP}\times 100\times 5)/\ ((2^{15}-1)\times \text{PLLN})$$

As a result:

$$\text{md}_{\text{quantized}}\% = (250\times 126\times 100\times 5)/\ ((2^{15}-1)\times 240) = 2.002\%\text{(peak)}$$

Figure 35 and *Figure 36* show the main PLL output clock waveforms in center spread and down spread modes, where:

F0 is f_{PLL_OUT} nominal.

T_{mode} is the modulation period.

md is the modulation depth.

Figure 35. PLL output clock waveforms in center spread mode

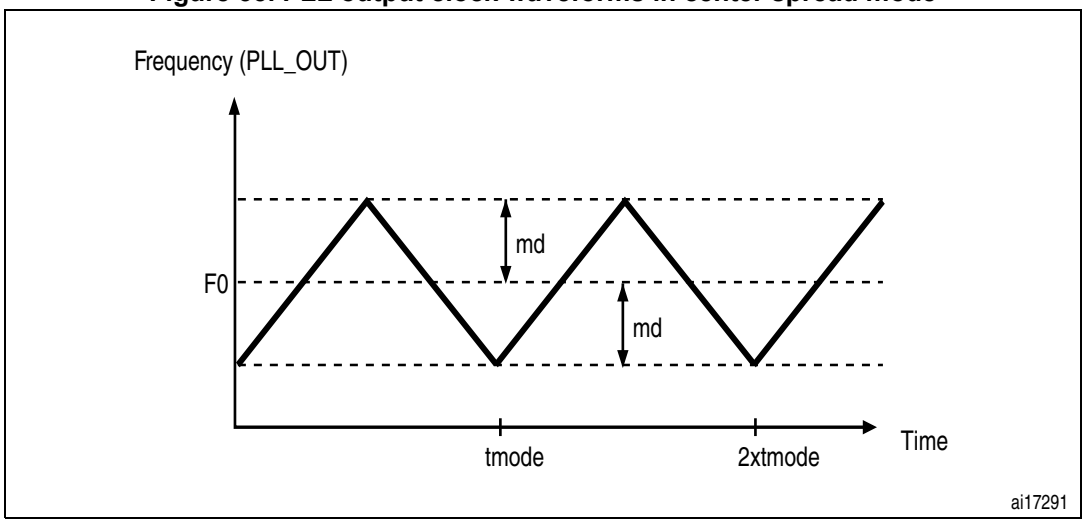
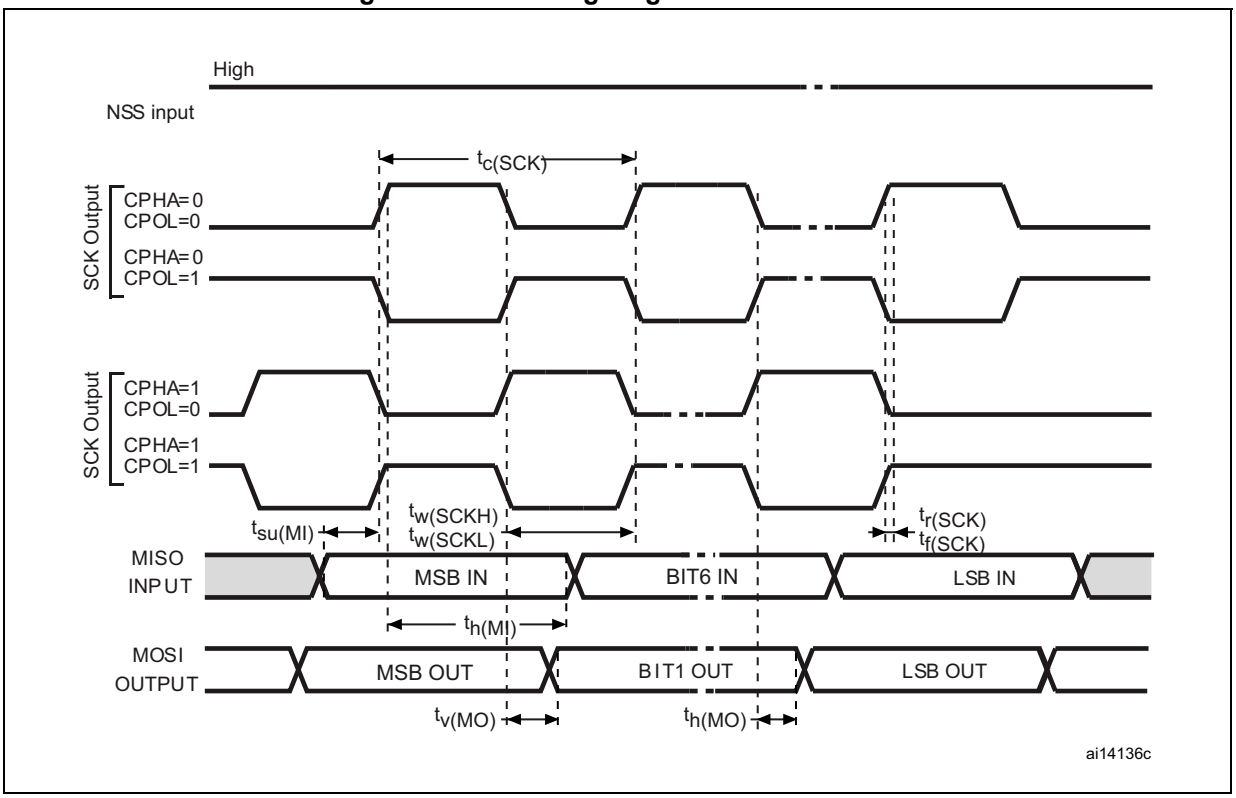


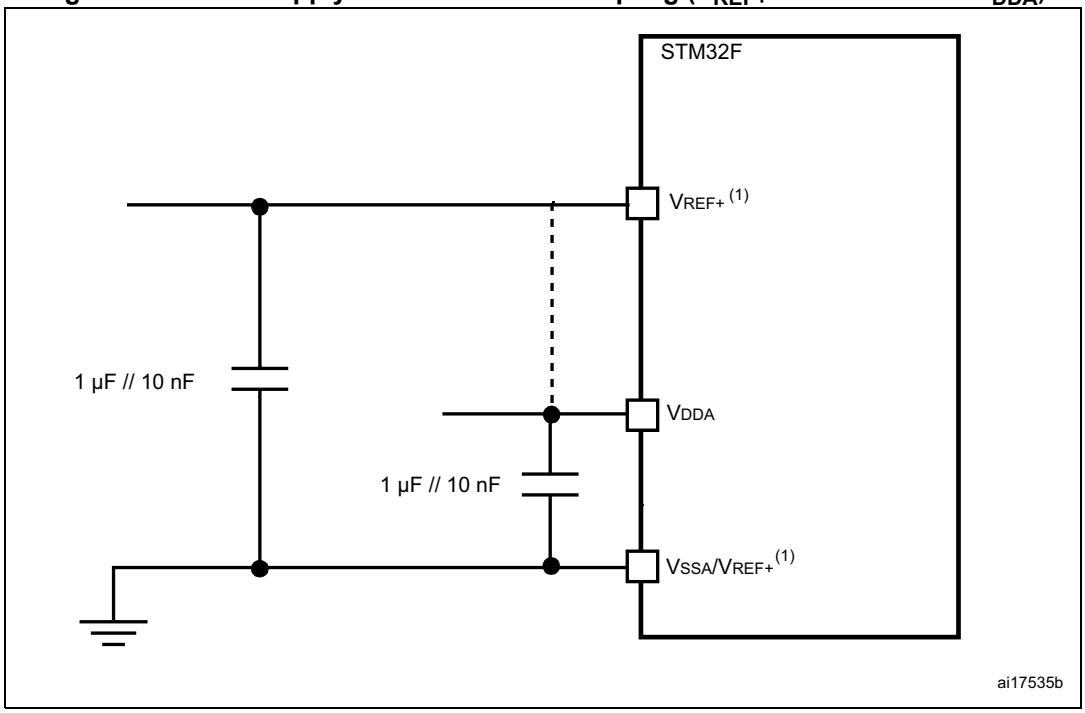
Figure 41. SPI timing diagram - master mode



General PCB design guidelines

Power supply decoupling should be performed as shown in *Figure 51* or *Figure 52*, depending on whether V_{REF+} is connected to V_{DDA} or not. The 10 nF capacitors should be ceramic (good quality). They should be placed them as close as possible to the chip.

Figure 51. Power supply and reference decoupling (V_{REF+} not connected to V_{DDA})



1. V_{REF+} and V_{REF-} inputs are both available on UFBGA176. V_{REF+} is also available on LQFP100, LQFP144, and LQFP176. When V_{REF+} and V_{REF-} are not available, they are internally connected to V_{DDA} and V_{SSA}.

Table 74. DAC characteristics (continued)

Symbol	Parameter	Min	Typ	Max	Unit	Comments
Offset(4)	Offset error (difference between measured value at Code (0x800) and the ideal value = V_{REF+}/2)	-	-	±10	mV	Given for the DAC in 12-bit configuration
		-	-	±3	LSB	Given for the DAC in 10-bit at V_{REF+} = 3.6 V
		-	-	±12	LSB	Given for the DAC in 12-bit at V_{REF+} = 3.6 V
Gain error(4)	Gain error	-	-	±0.5	%	Given for the DAC in 12-bit configuration
$t_{SETTLING}$(4)	Settling time (full scale: for a 10-bit input code transition between the lowest and the highest input codes when DAC_OUT reaches final value ±4LSB	-	3	6	µs	$C_{LOAD} \leq 50$ pF, $R_{LOAD} \geq 5$ kΩ
THD(4)	Total Harmonic Distortion Buffer ON	-	-	-	dB	$C_{LOAD} \leq 50$ pF, $R_{LOAD} \geq 5$ kΩ
Update rate(2)	Max frequency for a correct DAC_OUT change when small variation in the input code (from code i to i+1LSB)	-	-	1	MS/s	$C_{LOAD} \leq 50$ pF, $R_{LOAD} \geq 5$ kΩ
t_{WAKEUP}(4)	Wakeup time from off state (Setting the ENx bit in the DAC Control register)	-	6.5	10	µs	$C_{LOAD} \leq 50$ pF, $R_{LOAD} \geq 5$ kΩ input code between lowest and highest possible ones.
PSRR+ (2)	Power supply rejection ratio (to V_{DDA}) (static DC measurement)	-	–67	–40	dB	No R_{LOAD}, C_{LOAD} = 50 pF

1. V_{DD}/V_{DDA} minimum value of 1.7 V is obtained when the device operates in reduced temperature range, and with the use of an external power supply supervisor (refer to *Section : Internal reset OFF*).
2. Guaranteed by design.
3. The quiescent mode corresponds to a state where the DAC maintains a stable output level to ensure that no dynamic consumption occurs.
4. Guaranteed by characterization.

Figure 56. Asynchronous multiplexed PSRAM/NOR read waveforms

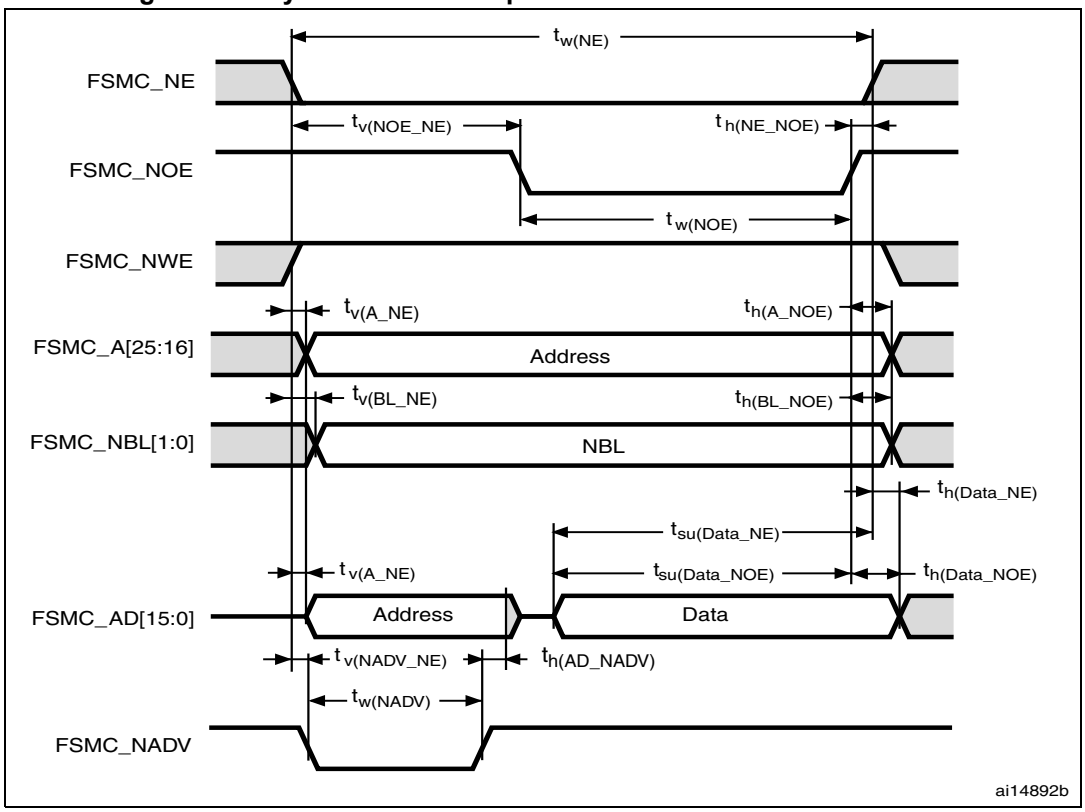
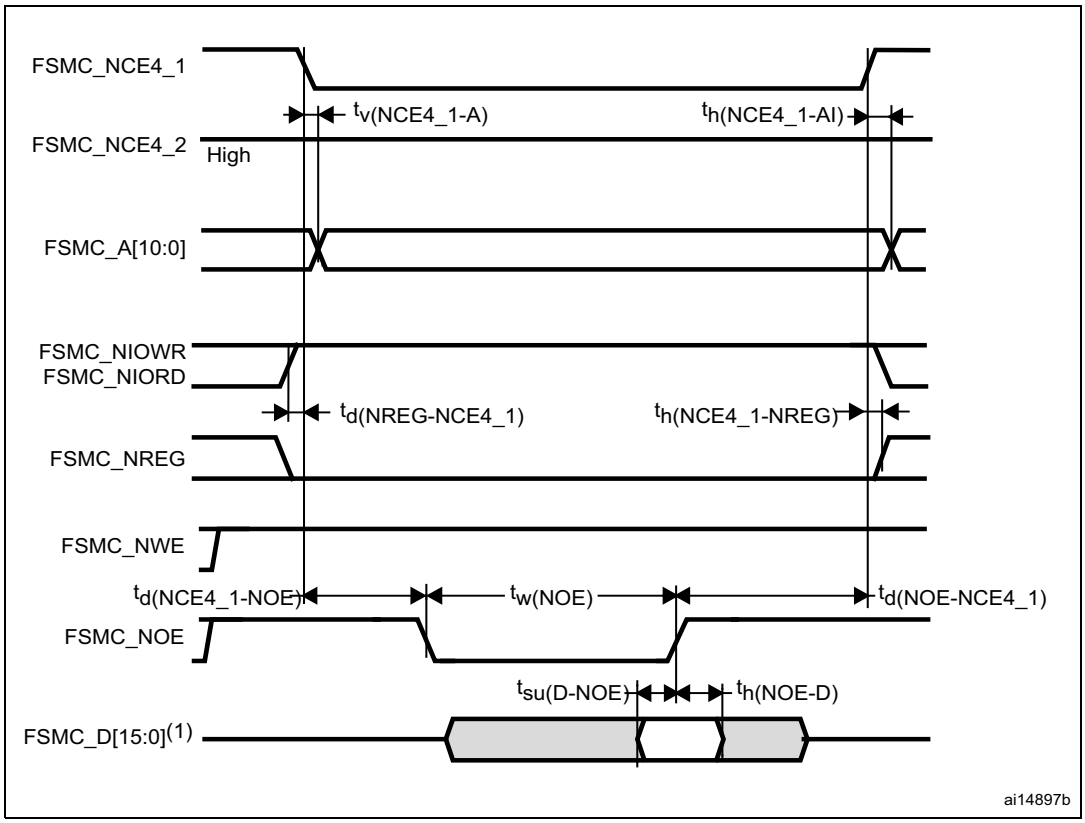


Table 77. Asynchronous multiplexed PSRAM/NOR read timings(1)(2)

Symbol	Parameter	Min	Max	Unit
$t_{w(NE)}$	FSMC_NE low time	$3T_{HCLK}-1$	$3T_{HCLK}+1$	ns
$t_{v(NOE\_NE)}$	FSMC_NEx low to FSMC_NOE low	$2T_{HCLK}-0.5$	$2T_{HCLK}+0.5$	ns
$t_{w(NOE)}$	FSMC_NOE low time	$T_{HCLK}-1$	$T_{HCLK}+1$	ns
$t_{h(NE\_NOE)}$	FSMC_NOE high to FSMC_NE high hold time	0	-	ns
$t_{v(A\_NE)}$	FSMC_NEx low to FSMC_A valid	-	3	ns
$t_{v(NADV\_NE)}$	FSMC_NEx low to FSMC_NADV low	1	2	ns
$t_{w(NADV)}$	FSMC_NADV low time	$T_{HCLK}-2$	$T_{HCLK}+1$	ns
$t_{h(AD\_NADV)}$	FSMC_AD(adress) valid hold time after FSMC_NADV high)	T_{HCLK}	-	ns
$t_{h(A\_NOE)}$	Address hold time after FSMC_NOE high	$T_{HCLK}-1$	-	ns
$t_{h(BL\_NOE)}$	FSMC_BL time after FSMC_NOE high	0	-	ns
$t_{v(BL\_NE)}$	FSMC_NEx low to FSMC_BL valid	-	2	ns
$t_{su(Data\_NE)}$	Data to FSMC_NEx high setup time	$T_{HCLK}+4$	-	ns
$t_{su(Data\_NOE)}$	Data to FSMC_NOE high setup time	$T_{HCLK}+4$	-	ns
$t_{h(Data\_NE)}$	Data hold time after FSMC_NEx high	0	-	ns
$t_{h(Data\_NOE)}$	Data hold time after FSMC_NOE high	0	-	ns

1. C_L = 30 pF.
2. Guaranteed by characterization.

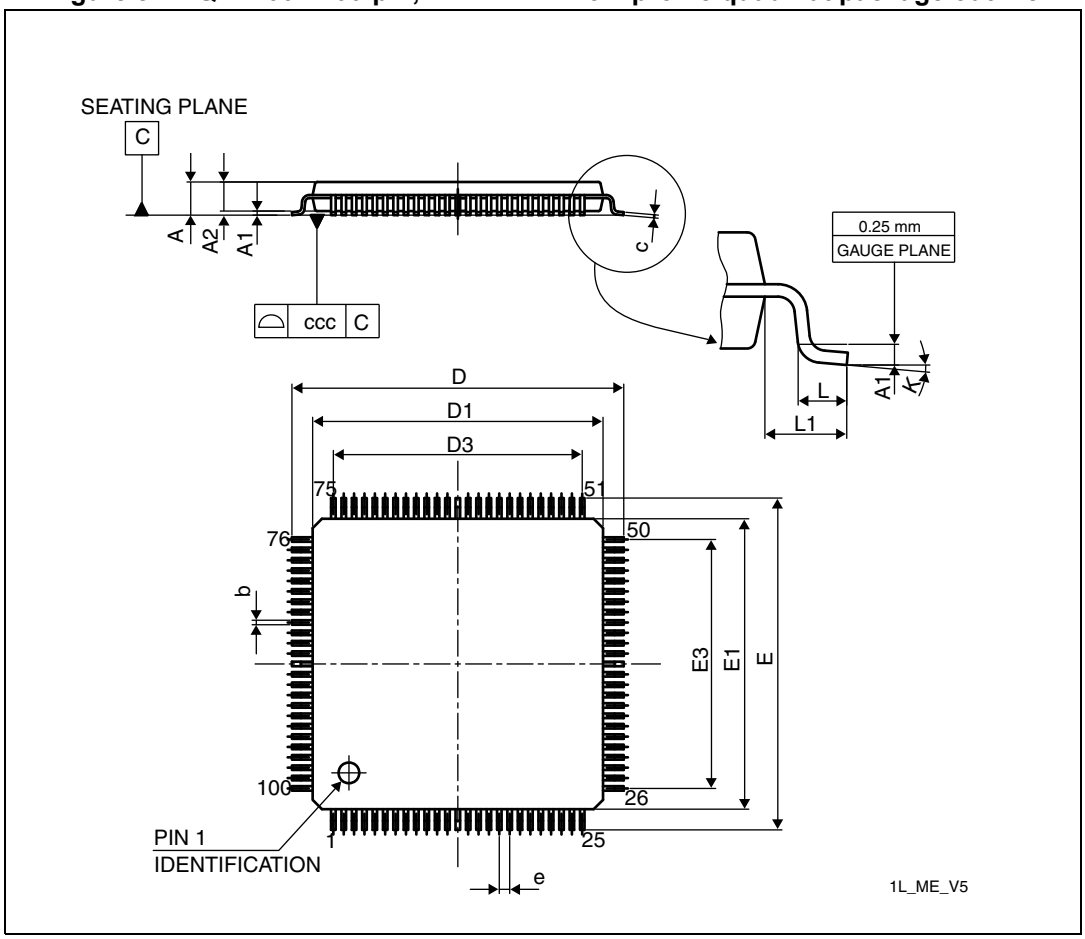
Figure 64. PC Card/CompactFlash controller waveforms for attribute memory read access



1. Only data bits 0...7 are read (bits 8...15 are disregarded).

6.3 LQPF100 package information

Figure 81. LQFP100 - 100-pin, 14 x 14 mm low-profile quad flat package outline



1. Drawing is not to scale.

Table 93. LQPF100 – 100-pin, 14 x 14 mm low-profile quad flat package mechanical data(1)

Symbol	millimeters			inches		
	Min	Typ	Max	Min	Typ	Max
A	-	-	1.600	-	-	0.0630
A1	0.050	-	0.150	0.0020	-	0.0059
A2	1.350	1.400	1.450	0.0531	0.0551	0.0571
b	0.170	0.220	0.270	0.0067	0.0087	0.0106
c	0.090	-	0.200	0.0035	-	0.0079
D	15.800	16.000	16.200	0.6220	0.6299	0.6378
D1	13.800	14.000	14.200	0.5433	0.5512	0.5591
D3	-	12.000	-	-	0.4724	-
E	15.80	16.000	16.200	0.6220	0.6299	0.6378

6.7 Thermal characteristics

The maximum chip-junction temperature, T_J max, in degrees Celsius, may be calculated using the following equation:

T_J max = T_A max + (P_D max x Θ_{JA})

Where:

- T_A max is the maximum ambient temperature in °C,
- Θ_{JA} is the package junction-to-ambient thermal resistance, in °C/W,
- P_D max is the sum of P_{INT} max and $P_{I/O}$ max (P_D max = P_{INT} max + $P_{I/O}$max),
- P_{INT} max is the product of I_{DD} and V_{DD}, expressed in Watts. This is the maximum chip internal power.

$P_{I/O}$ max represents the maximum power dissipation on output pins where:

$P_{I/O}$ max = Σ (V_{OL} × I_{OL}) + Σ((V_{DD} – V_{OH}) × I_{OH}),

taking into account the actual V_{OL} / I_{OL} and V_{OH} / I_{OH} of the I/Os at low and high level in the application.

Table 98. Package thermal characteristics

Symbol	Parameter	Value	Unit
Θ_{JA}	**Thermal resistance junction-ambient** LQFP64 - 10 × 10 mm / 0.5 mm pitch	46	°C/W
	Thermal resistance junction-ambient LQFP100 - 14 × 14 mm / 0.5 mm pitch	43	
	Thermal resistance junction-ambient LQFP144 - 20 × 20 mm / 0.5 mm pitch	40	
	Thermal resistance junction-ambient LQFP176 - 24 × 24 mm / 0.5 mm pitch	38	
	Thermal resistance junction-ambient UFBGA176 - 10× 10 mm / 0.65 mm pitch	39	
	Thermal resistance junction-ambient WLCSP90 - 0.400 mm pitch	38.1	

Reference document

JESD51-2 Integrated Circuits Thermal Test Method Environment Conditions - Natural Convection (Still Air). Available from www.jedec.org.

8 Revision history

Table 100. Document revision history

Date	Revision	Changes
15-Sep-2011	1	Initial release.
24-Jan-2012	2	Added WLCSP90 package on cover page. Renamed USART4 and USART5 into UART4 and UART5, respectively. Updated number of USB OTG HS and FS in *Table 2: STM32F405xx and STM32F407xx: features and peripheral counts*. Updated *Figure 3: Compatible board design between STM32F10xx/STM32F2/STM32F40xxx for LQFP144 package* and *Figure 4: Compatible board design between STM32F2 and STM32F40xxx for LQFP176 and BGA176 packages*, and removed note 1 and 2. Updated *Section 2.2.9: Flexible static memory controller (FSMC)*. Modified I/Os used to reprogram the Flash memory for CAN2 and USB OTG FS in *Section 2.2.13: Boot modes*. Updated note in *Section 2.2.14: Power supply schemes*. PDR_ON no more available on LQFP100 package. Updated *Section 2.2.16: Voltage regulator*. Updated condition to obtain a minimum supply voltage of 1.7 V in the whole document. Renamed USART4/5 to UART4/5 and added LIN and IrDA feature for UART4 and UART5 in *Table 5: USART feature comparison*. Removed support of I2C for OTG PHY in *Section 2.2.30: Universal serial bus on-the-go full-speed (OTG_FS)*. Added *Table 6: Legend/abbreviations used in the pinout table*. *Table 7: STM32F40xxx pin and ball definitions*: replaced V_{SS}_3, V_{SS}_4, and V_{SS}_8 by V_{SS}; reformatted *Table 7: STM32F40xxx pin and ball definitions* to better highlight I/O structure, and alternate functions versus additional functions; signal corresponding to LQFP100 pin 99 changed from PDR_ON to V_{SS}; EVENTOUT added in the list of alternate functions for all I/Os; ADC3_IN8 added as alternate function for PF10; FSMC_CLE and FSMC_ALE added as alternate functions for PD11 and PD12, respectively; PH10 alternate function TIM15_CH1_ETR renamed TIM5_CH1; updated PA4 and PA5 I/O structure to TTa. Removed OTG_HS_SCL, OTG_HS_SDA, OTG_FS_INTN in *Table 7: STM32F40xxx pin and ball definitions* and *Table 9: Alternate function mapping*. Changed TCM data RAM to CCM data RAM in *Figure 18: STM32F40xxx memory map*. Added I_{VDD} and I_{VSS} maximum values in *Table 12: Current characteristics*. Added *Note 1* related to f_{HCLK}, updated *Note 2* in *Table 14: General operating conditions*, and added maximum power dissipation values. Updated *Table 15: Limitations depending on the operating power supply range*.

Table 100. Document revision history (continued)

Date	Revision	Changes
22-Oct-2015	6	In the whole document, updated notes related to values guaranteed by design or by characterization. Updated *Table 34: HSI oscillator characteristics*. Changed f_{VCO_OUT} minimum value and VCO freq to 100 MHz in *Table 36: Main PLL characteristics* and *Table 37: PLLI2S (audio PLL) characteristics*. Updated *Figure 39: SPI timing diagram - slave mode and CPHA = 0*. Updated *Figure 53: 12-bit buffered /non-buffered DAC*. Removed note 1 related to better performance using a restricted V_{DD} range in *Table 68: ADC accuracy at fADC = 30 MHz*. Upated *Figure 84: LQFP144 - 144-pin, 20 x 20 mm low-profile quad flat package outline*. Updated *Figure 87: UFBGA176+25 ball, 10 x 10 mm, 0.65 mm pitch, ultra fine pitch ball grid array package outline* and *Table 95: UFBGA176+25 ball, 10 × 10 × 0.65 mm pitch, ultra thin fine pitch ball grid array mechanical data*.
16-Mar-2016	7	Updated *Figure 2: Compatible board design STM32F10xx/STM32F2/STM32F40xxx for LQFP100 package*. Updated $\|V_{SSX}-V_{SS}\|$ in *Table 11: Voltage characteristics* to add V_{REF+} Added V_{REF-}in *Table 67: ADC characteristics*. Updated *Table 90: WLCSP90 - 4.223 x 3.969 mm, 0.400 mm pitch wafer level chip scale package mechanical data*.
09-Sep-2016	8	Remove note 1 below *Figure 5: STM32F40xxx block diagram*. Updated definition of stresses above maximum ratings in *Section 5.2: Absolute maximum ratings*. Updated $t_{h(NSS)}$) in *Figure 39: SPI timing diagram - slave mode and CPHA = 0Figure* and *Figure 40: SPI timing diagram - slave mode and CPHA = 1*. Added note related to optional marking and inset/upset marks in all package marking sections. Updated *Figure 87: UFBGA176+25 ball, 10 x 10 mm, 0.65 mm pitch, ultra fine pitch ball grid array package outline* and *Table 95: UFBGA176+25 ball, 10 × 10 × 0.65 mm pitch, ultra thin fine pitch ball grid array mechanical data*.